



Response Under 37 C.F.R. § 1.116
Expedited Procedure
Group Art Unit 2814

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION OF

LEE et al.

Appln. No.: 09/751,453

Filed: January 2, 2001

Title: METHOD FOR FABRICATING CAPACITORS FOR SEMICONDUCTOR DEVICES

*Cancelled
7/20/03 Q3 PM
He will call back
8/14/03*

November 20, 2002

* * * * *

AMENDMENT UNDER 37 C.F.R. § 1.116

Hon. Commissioner of Patents
Box AF
Washington, D.C. 20231

Sir:

In response to the Office Action dated August 20, 2002, please enter the following amendments and remarks:

IN THE CLAIMS:

Please amend claims 1, 19, and 20 as follows:

*J. Braunstein
5/22/03*

1. (Twice Amended) A method for fabricating a capacitor of a semiconductor device, the method comprising:

forming a lower electrode on a semiconductor substrate;

forming a dielectric layer on the lower electrode by

forming a first amorphous TaON thin film directly on the lower electrode;

annealing the first amorphous TaON thin film in an NH₃ atmosphere;

forming a second amorphous TaON thin film on the lower electrode; and

B1
annealing the second amorphous TaON thin film to form a multilayer TaON dielectric film; and

forming an upper electrode over the TaON dielectric film.